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Cont'd  
74 (new). The memory cell, as set forth in claim 62, wherein the memory material comprises a chalcogenide material.

75 (new). The memory cell, as set forth in claim 62, wherein the memory material comprises a programmable resistive element.

76 (new). The memory cell, as set forth in claim 75, wherein the programmable resistive element changes between different resistance levels in response to electrical stimulus.

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**REMARKS**

Claims 2-31 have been canceled without prejudice. New claims 32-76 have been added. Consideration of the application as amended is respectfully requested.

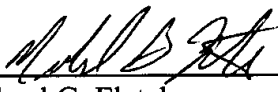
If the Examiner believes that a telephonic interview will help speed this application toward issuance, Applicants invite the Examiner to contact the undersigned at (281) 970-4545.

**General Authorization for Extensions of Time**

In accordance with 37 C.F.R. § 1.136, Applicants hereby provide a general authorization to treat this and any future reply requiring an extension of time as incorporating a request therefor. Furthermore, Applicants authorize the Commissioner to charge the appropriate fee for any extension of time to Deposit Account No. 13-3092; Order No. MCRO:106--2/FLE (95-0412.02).

Respectfully submitted,

Date: December 19, 2000

  
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